

FIG. 1A

PRIOR ART

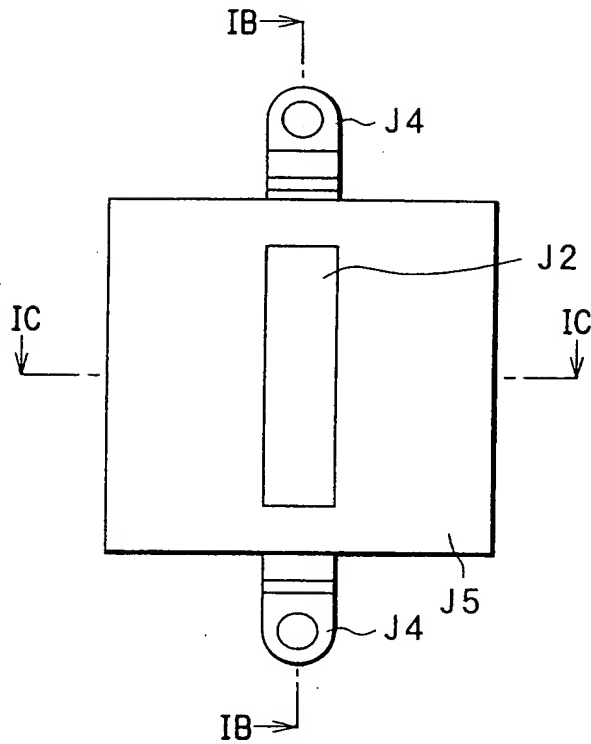


FIG. 1B

PRIOR ART

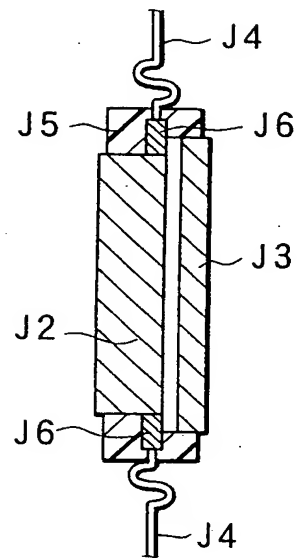


FIG. 1C

PRIOR ART

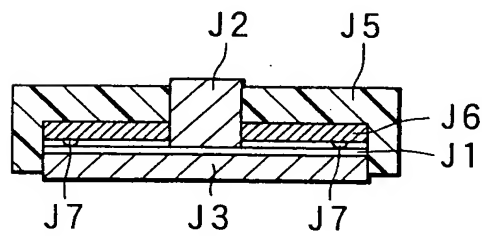


FIG. 2A

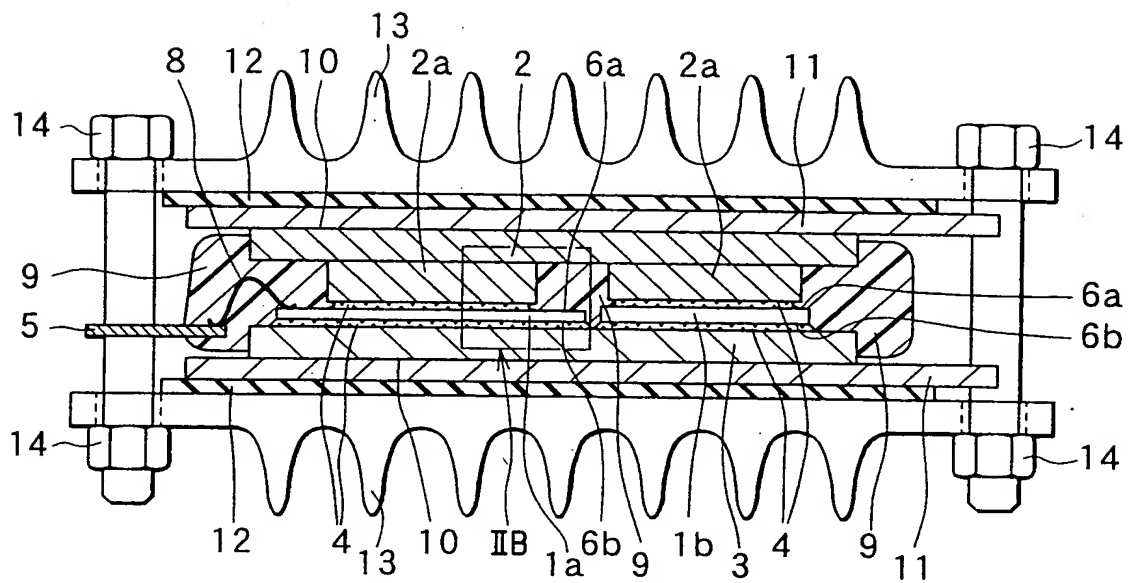


FIG. 2B

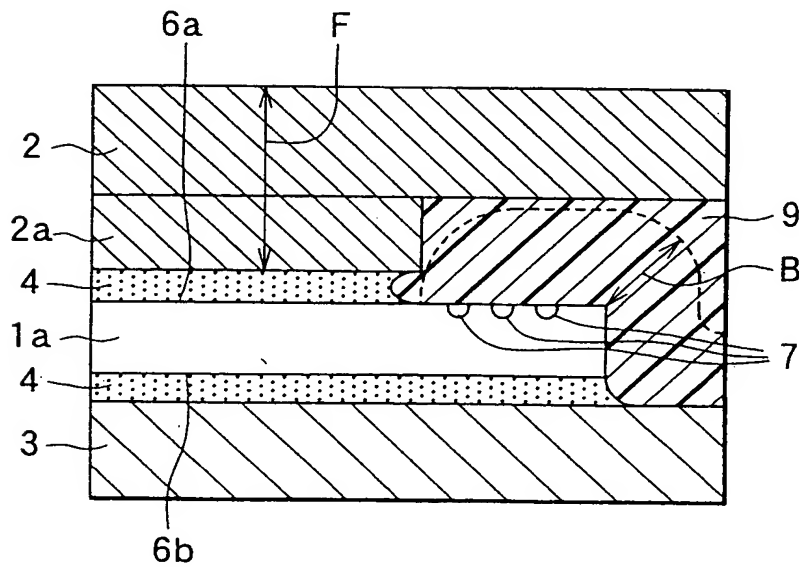


FIG. 3

NAME OF METAL	CHEMICAL COMPOSITION (%)													
	Fe	Zn	P	Ni	Si	Sn	NiB	Mn	Mg	Cr	Ti	B	Cu	Al
METAL a	2.3	0.1	0.03										REMAIN.	
METAL b	2.4	0.12	0.03										REMAIN.	
METAL c				3.0	0.7								REMAIN.	
METAL d	1.5	0.5				0.5							REMAIN.	
METAL e	1.0	0.05	0.1			1.0							REMAIN.	
METAL f	0.75		0.03			1.25							REMAIN.	
METAL g	0.05 0.15		0.025 0.040										REMAIN.	
METAL h	0.05 0.4		0.05 0.1			0.05 0.2	0.05 0.45						REMAIN.	
METAL i			0.15 OR LOWER	0.1 0.4		1.7 2.3							REMAIN.	
METAL j		0.2 0.35		3.0 3.4	0.6 0.75	1.0 1.5							REMAIN.	
METAL k	0.12 1.0	0.03 0.1			0.1 1.0			0.02 0.05	0.02 0.05		0.02 0.05		0.03 0.2	REMAIN.
METAL l	0.5	0.1			0.3 0.7			0.05	0.35 0.5	0.03		0.06	0.1	REMAIN.

FIG. 4A

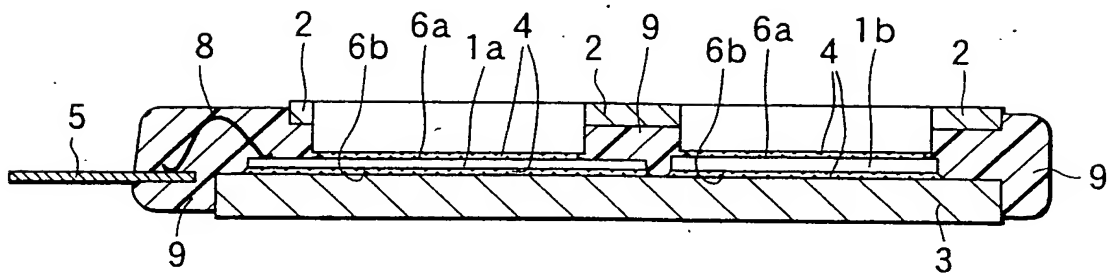


FIG. 4B

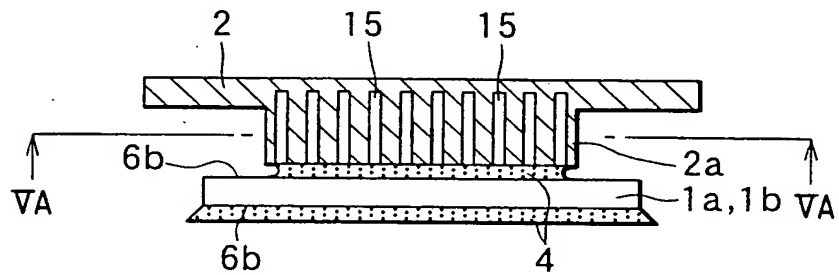


FIG. 4C

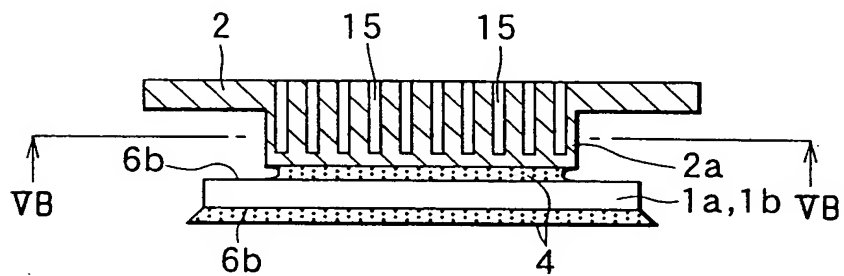


FIG. 4D

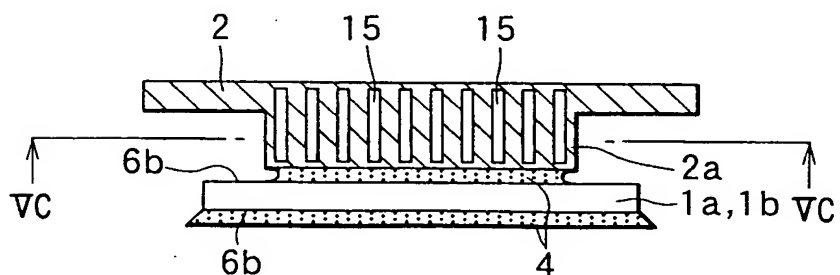


FIG. 5A

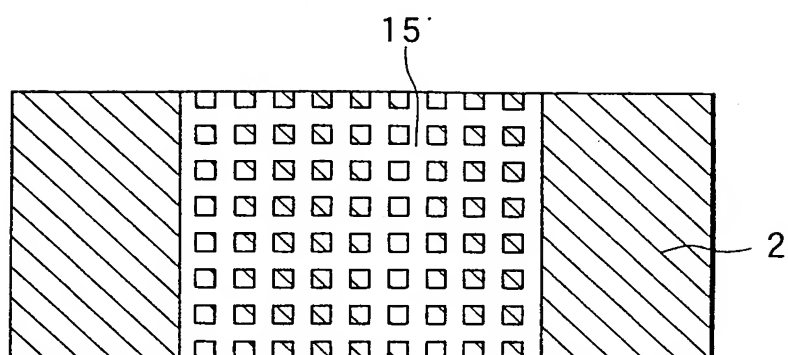


FIG. 5B

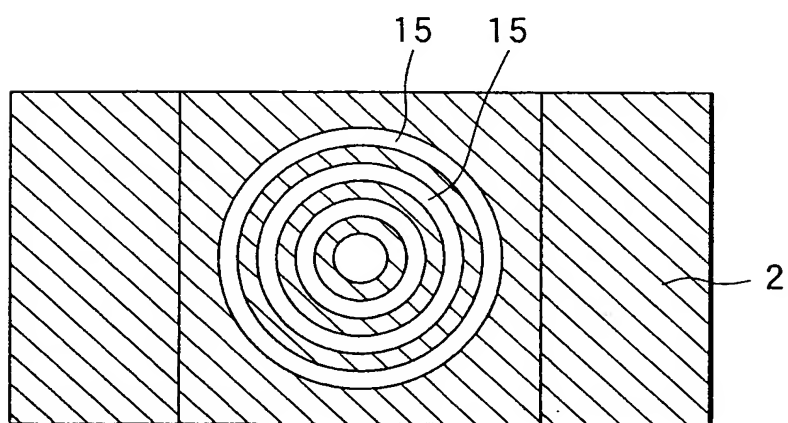


FIG. 5C

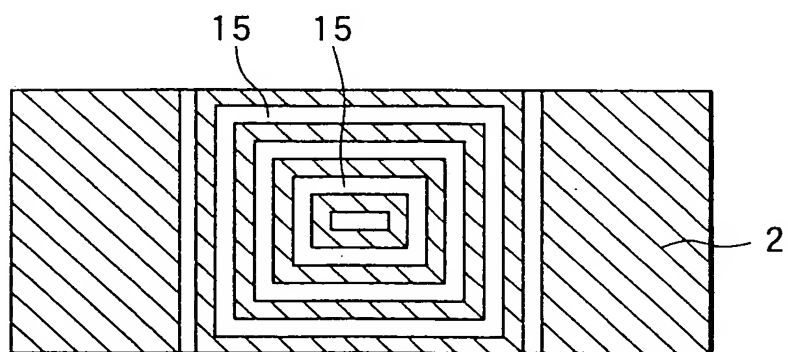


FIG. 6

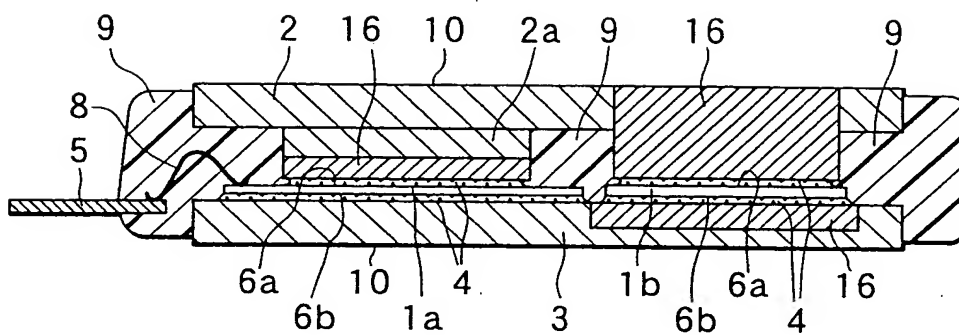


FIG. 7

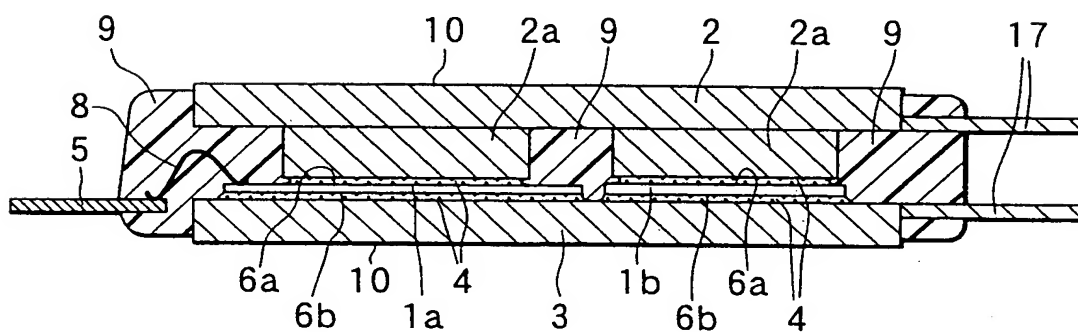


FIG. 8A

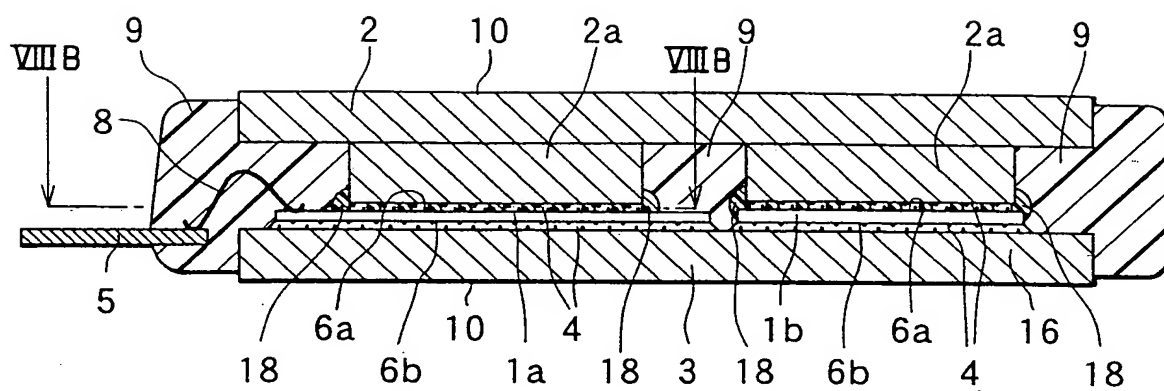
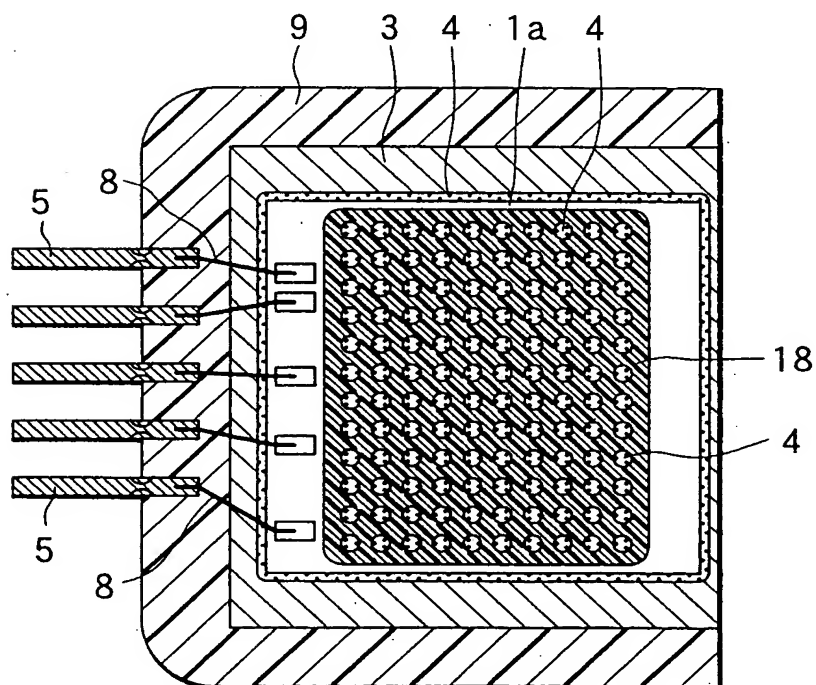


FIG. 8B



A cross-sectional view of a multi-layered structure. The structure consists of several layers: a top layer (2) with diagonal hatching, a layer (4) with a dotted pattern, a central layer (7) with a wavy line pattern, a layer (1a) with a solid white background, another layer (4) with a dotted pattern, and a bottom layer (3) with diagonal hatching. A horizontal layer (20) with diagonal hatching is positioned above the central layer (7). A vertical layer (9) with diagonal hatching is positioned to the right of the central layer (7). The central layer (7) is shown with a wavy line pattern, and the layer (1a) is shown with a solid white background.

FIG. 10

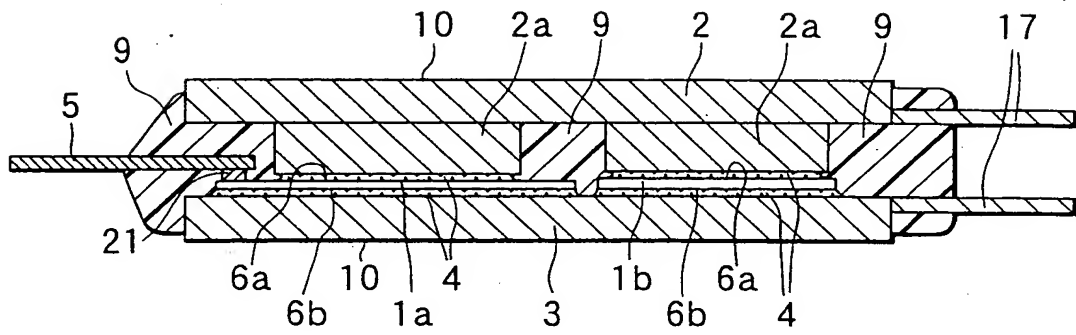


FIG. 11

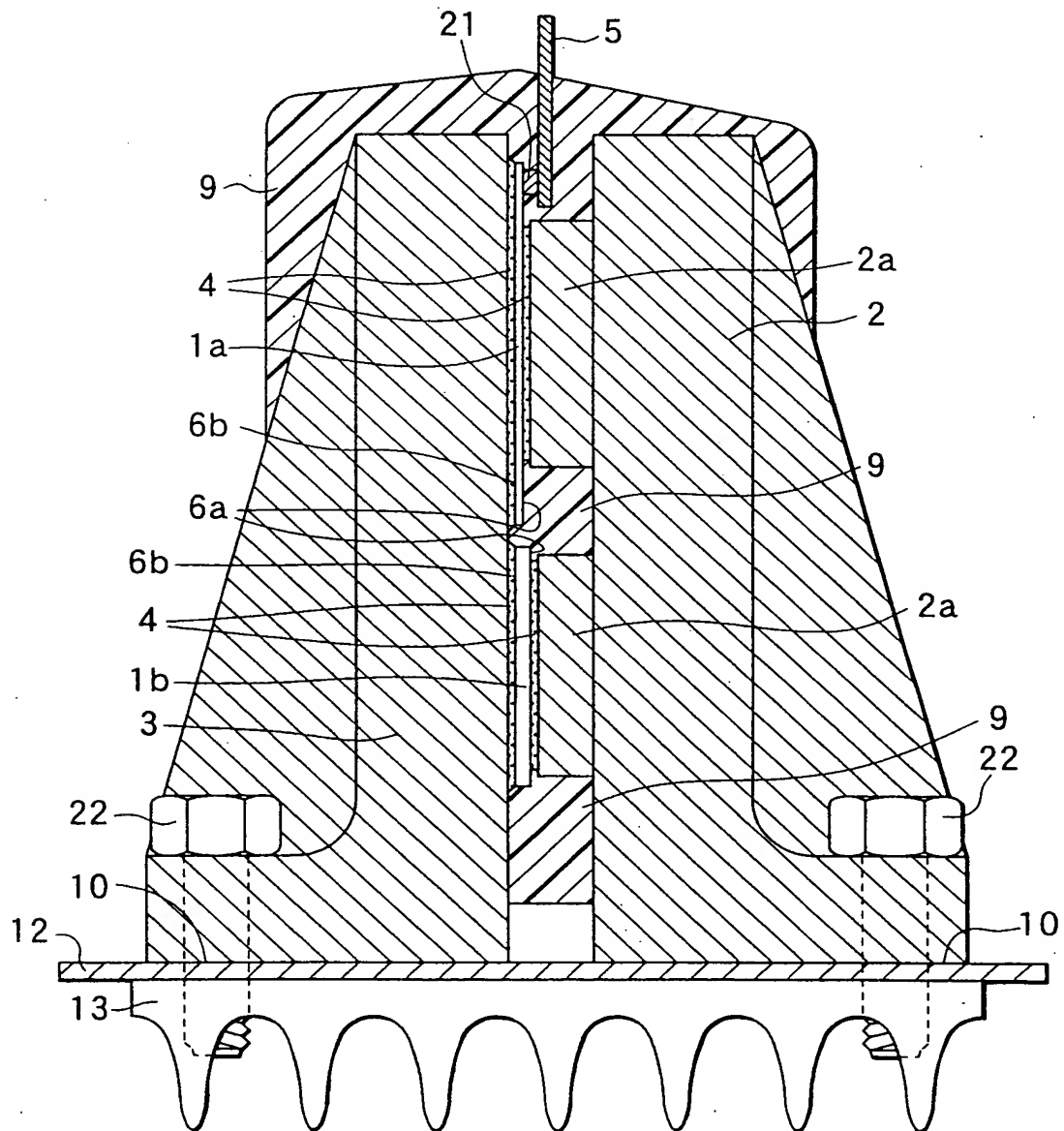
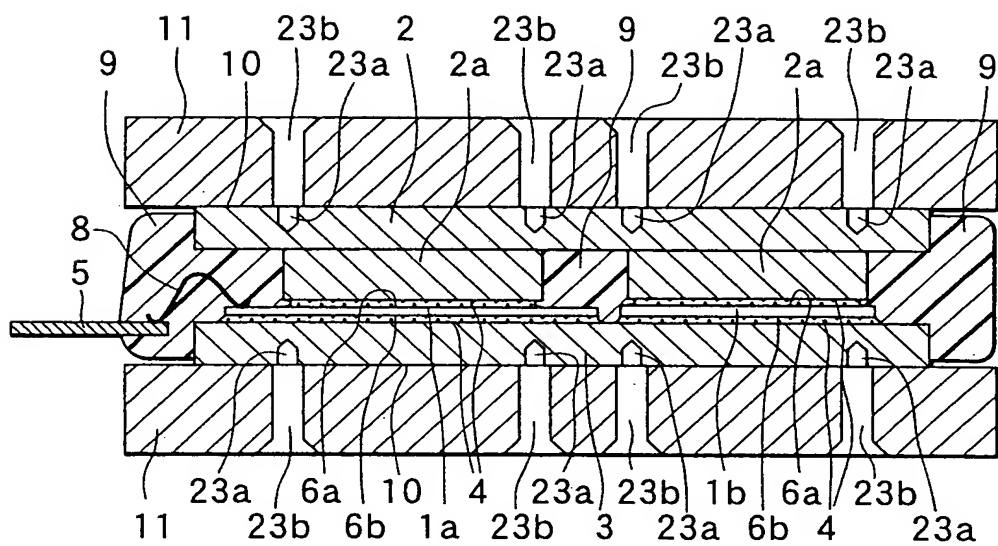


FIG. 12



This cross-sectional view shows a substrate 107 with a gate stack 106. The gate stack 106 is composed of a gate oxide layer 101 and a gate electrode layer 102. The channel region 101, 102 is located beneath the gate stack 106. The gate stack 106 is shown with a top surface 107a and a side surface 107c.

FIG. 16

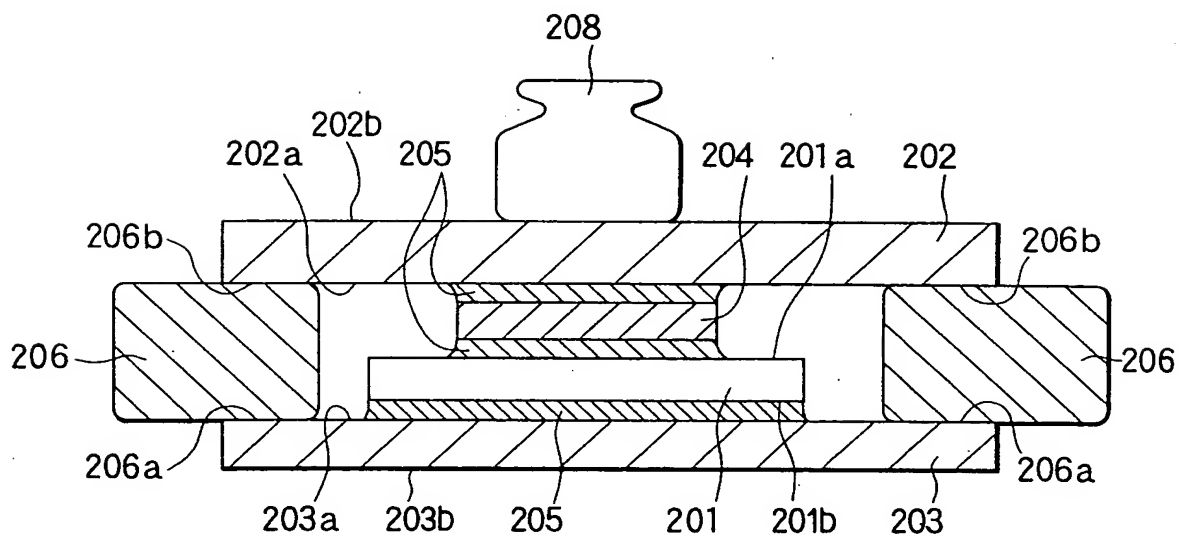


FIG. 17

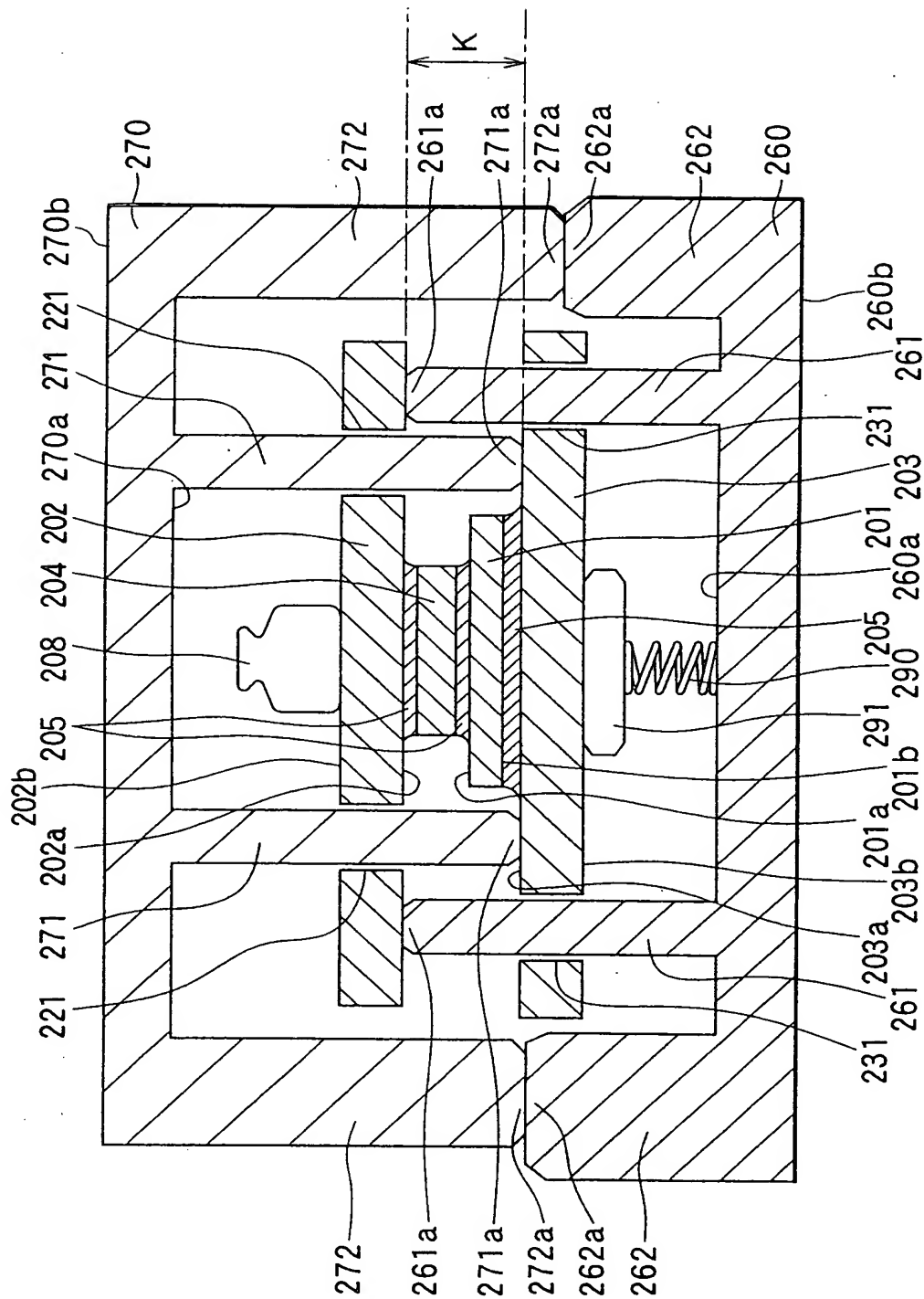


FIG. 18

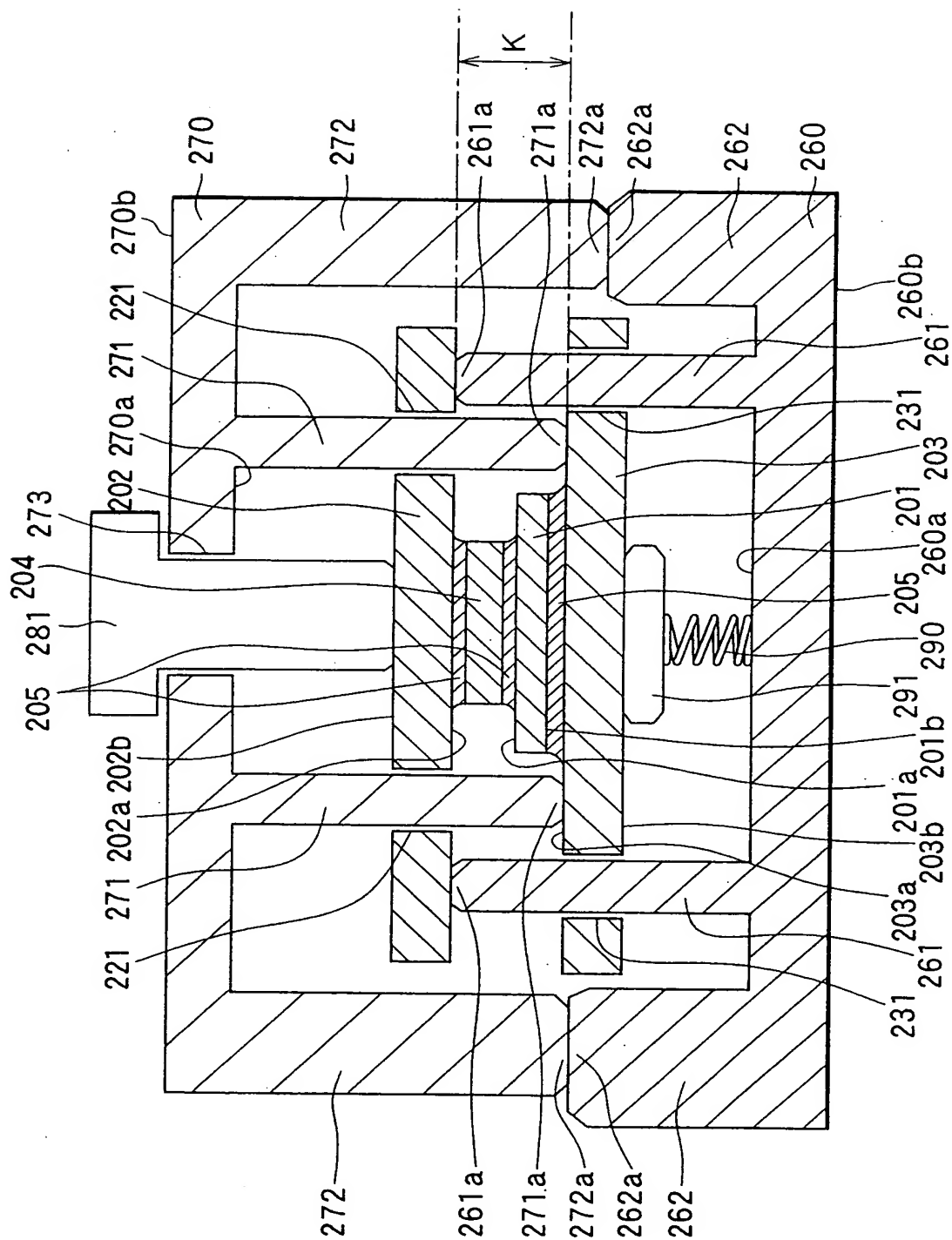


FIG. 19

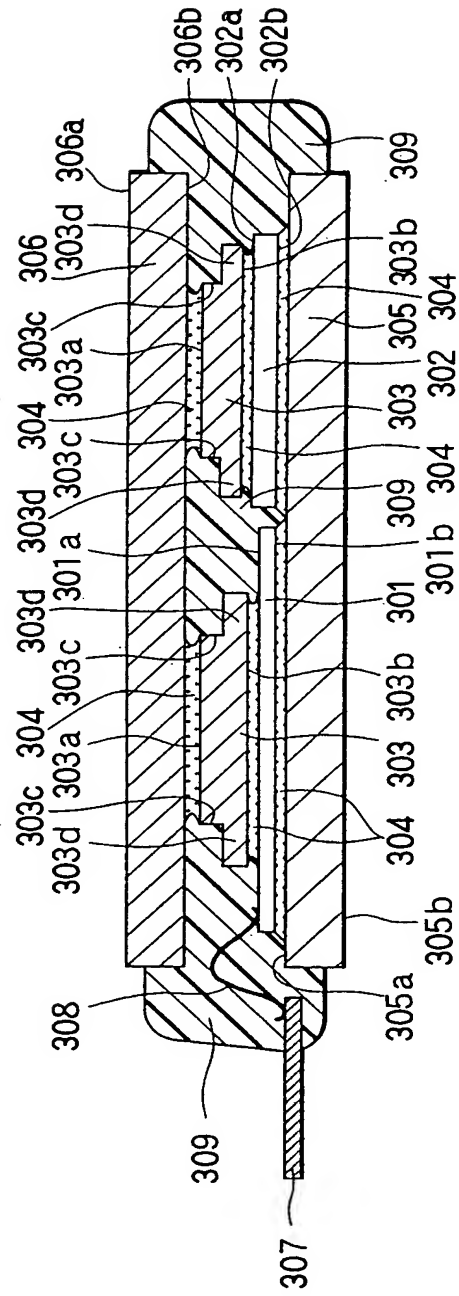


FIG. 20A

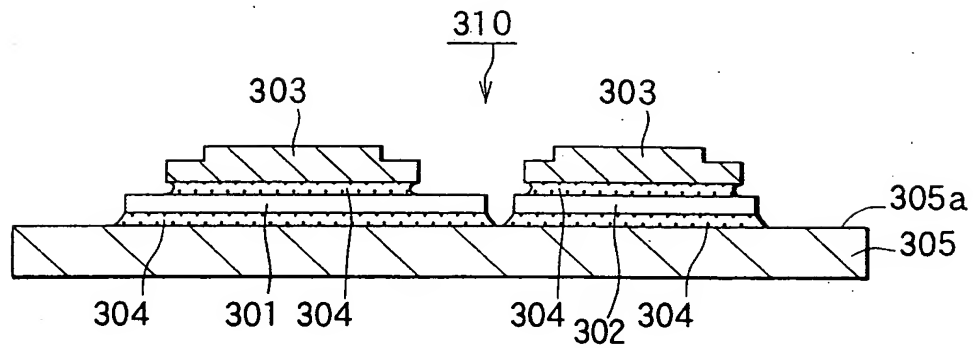


FIG. 20B

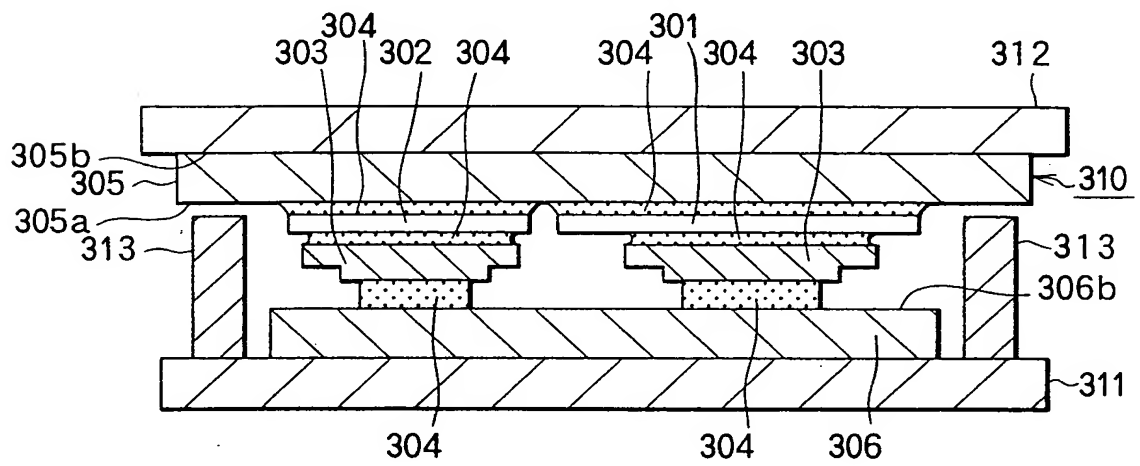


FIG. 20C

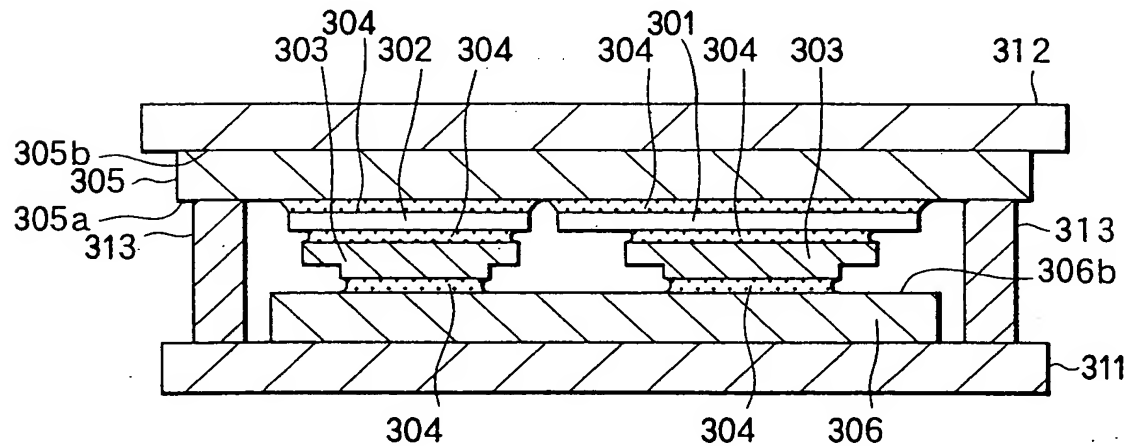


FIG. 21

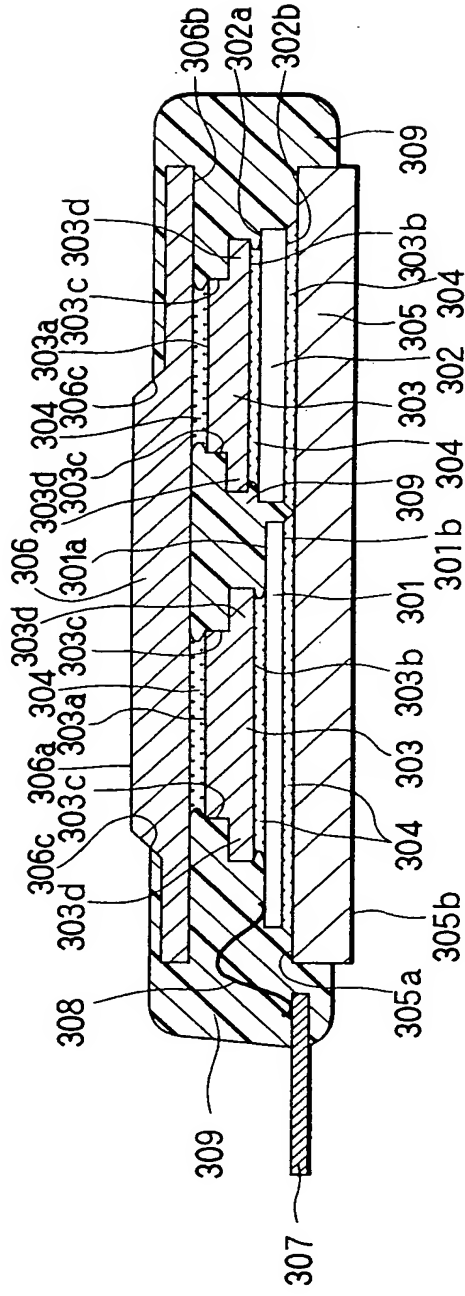


FIG. 22

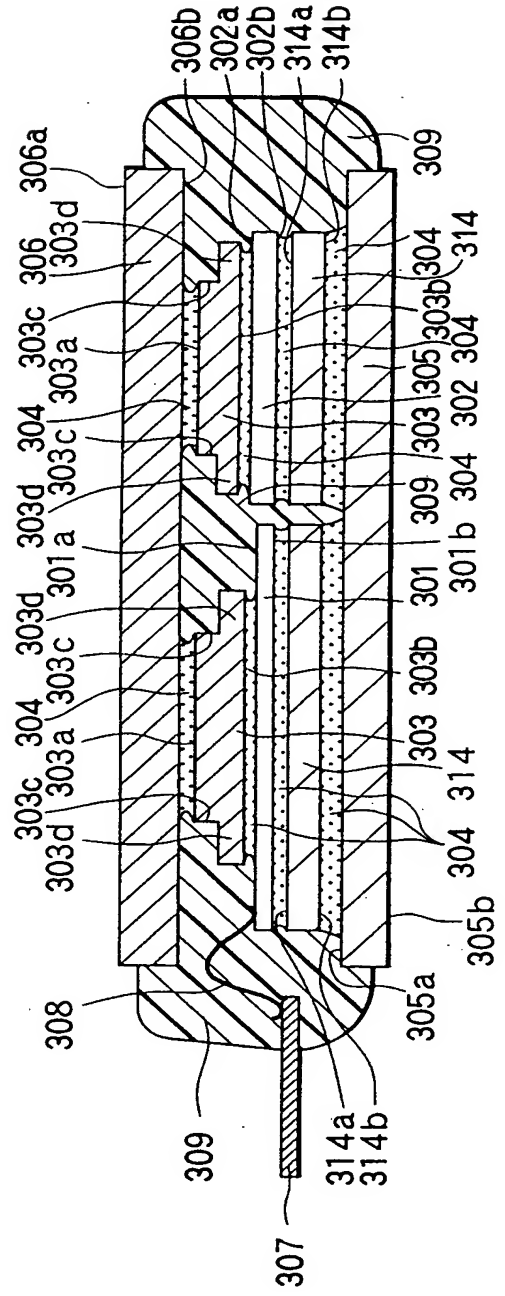


FIG. 23

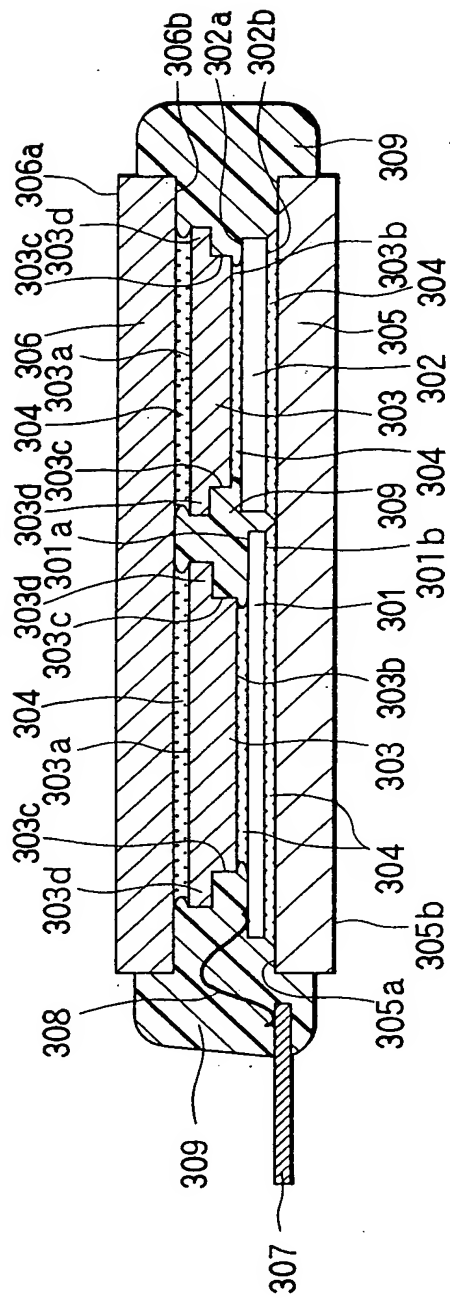


FIG. 24

XXVI

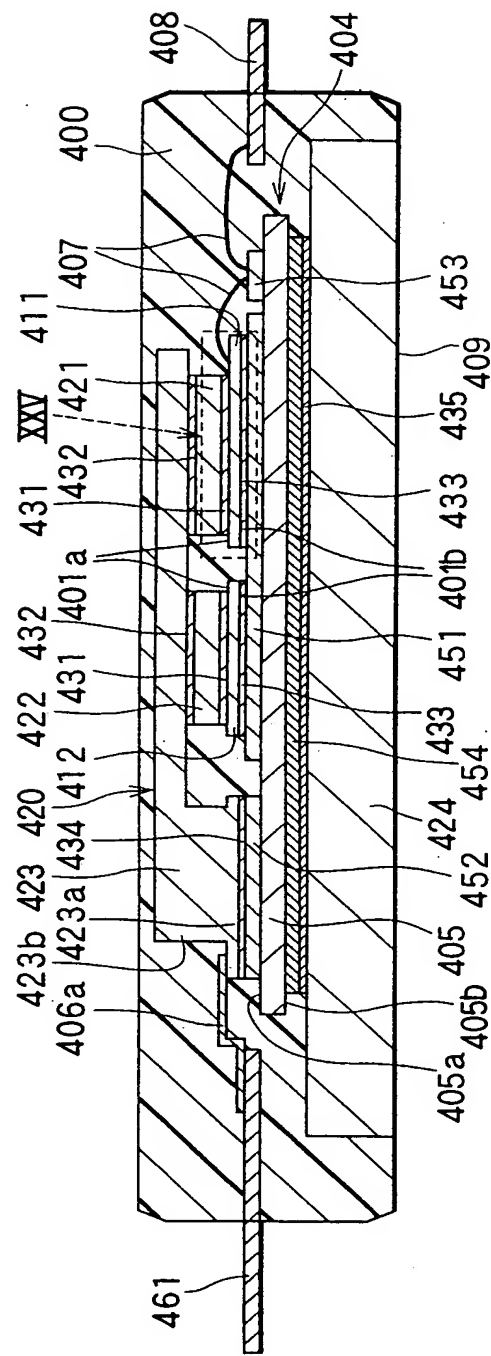


FIG. 25

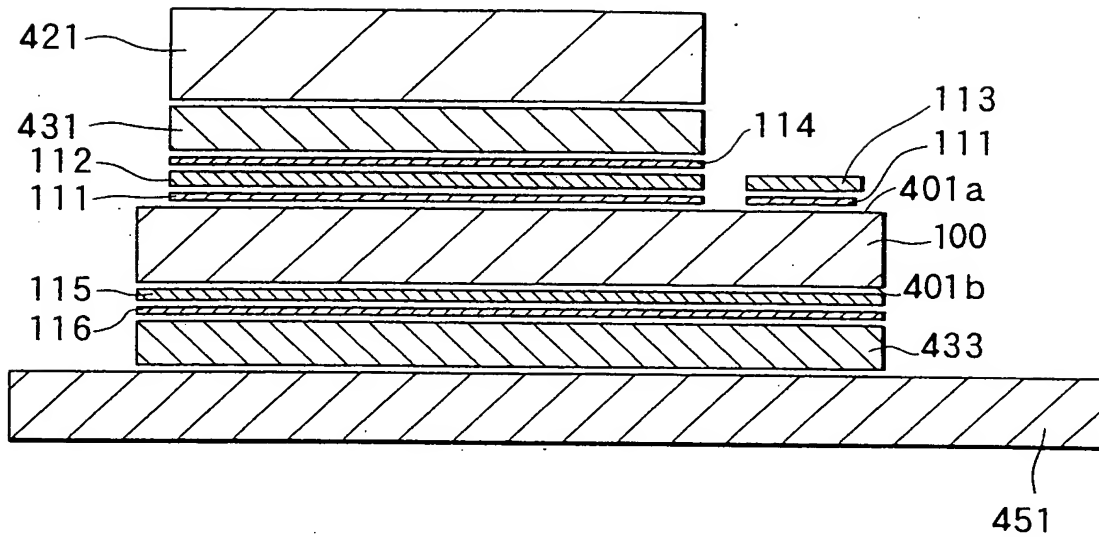


FIG. 26

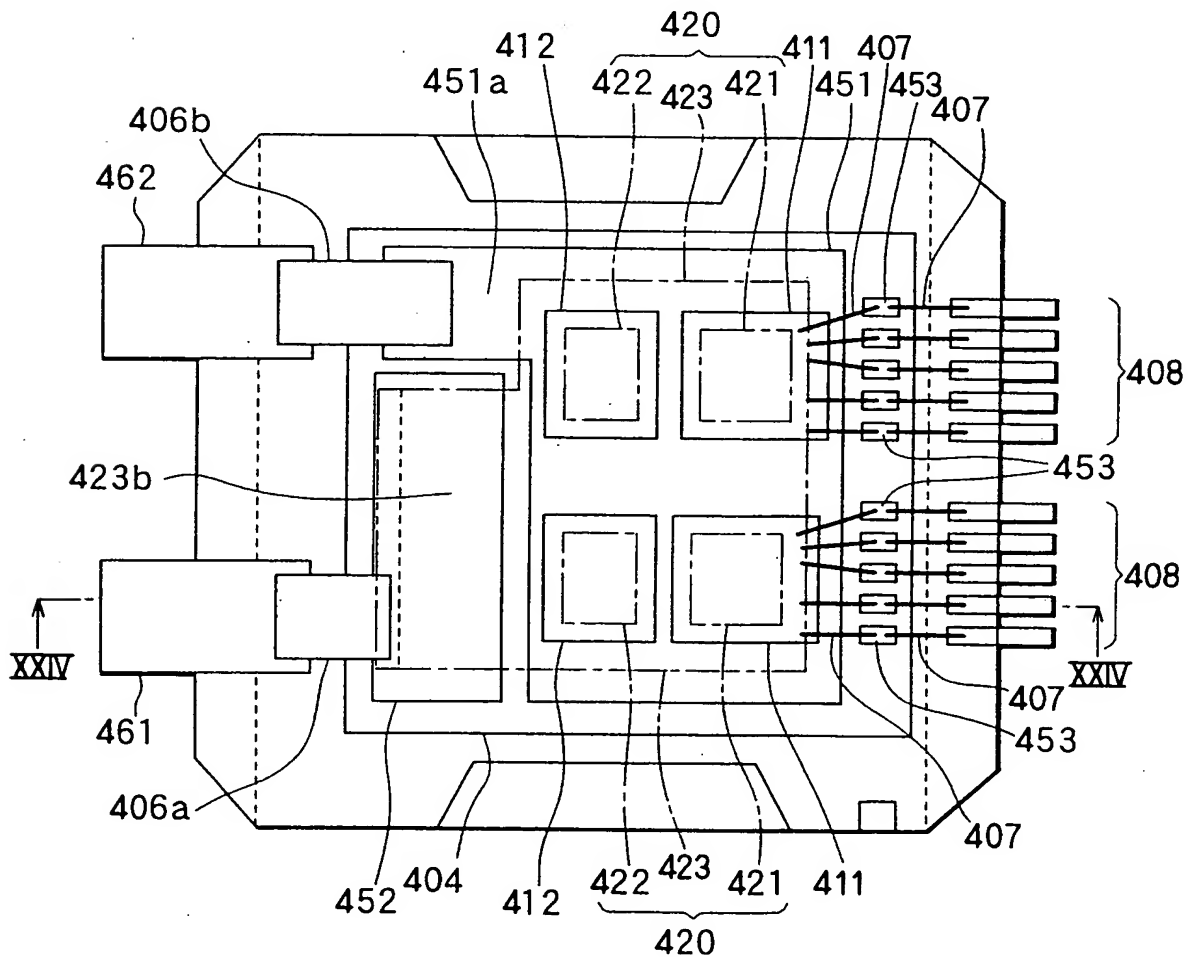


FIG. 27

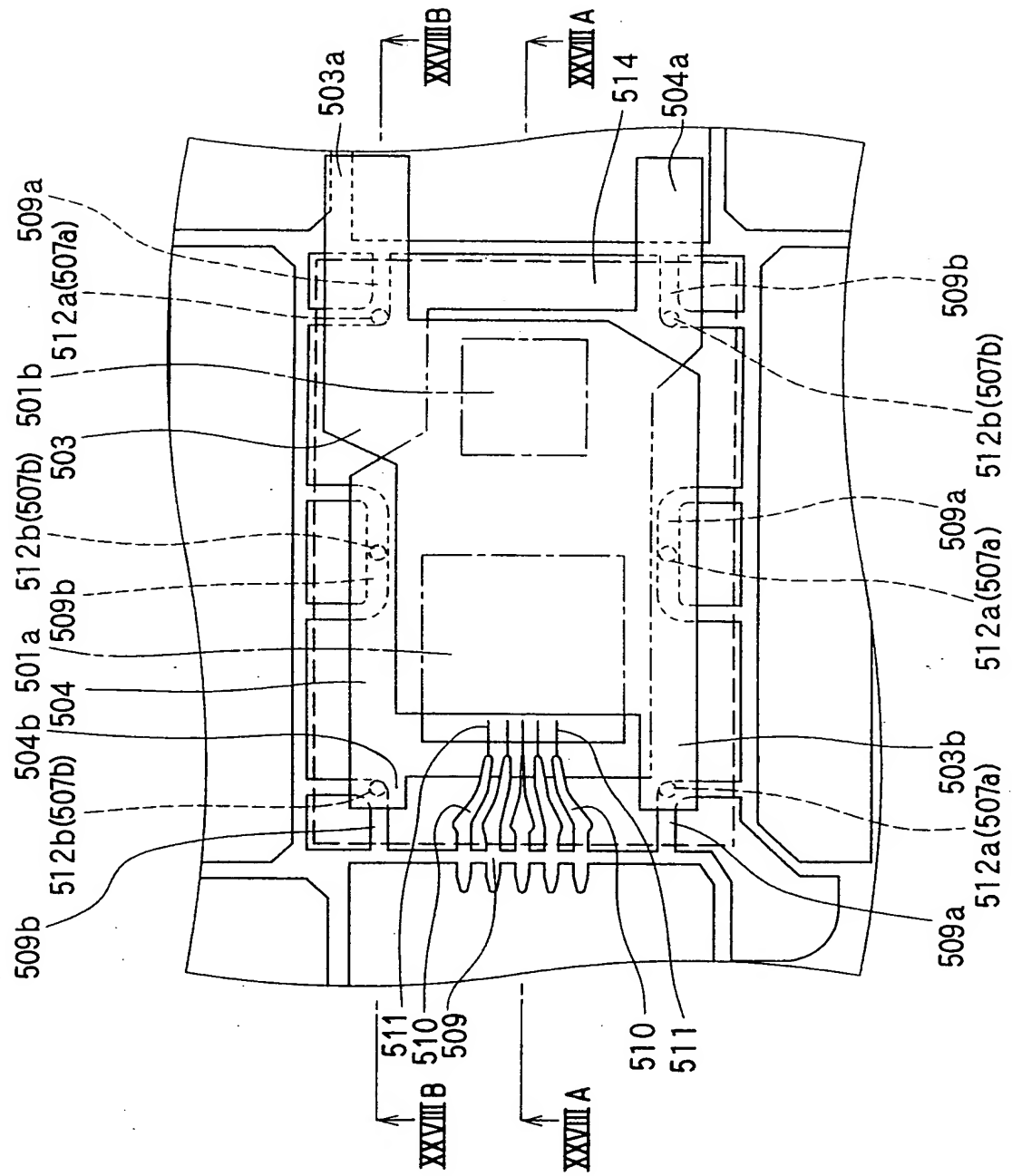


FIG. 28A

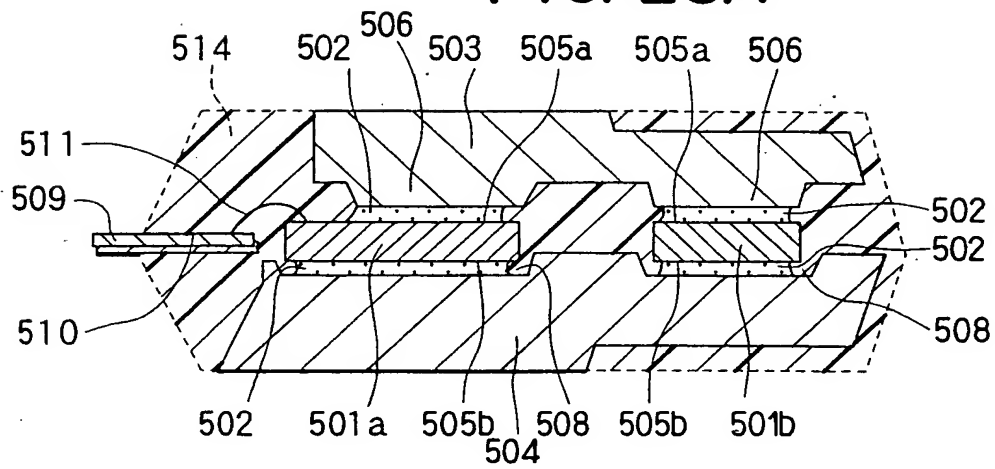


FIG. 28B

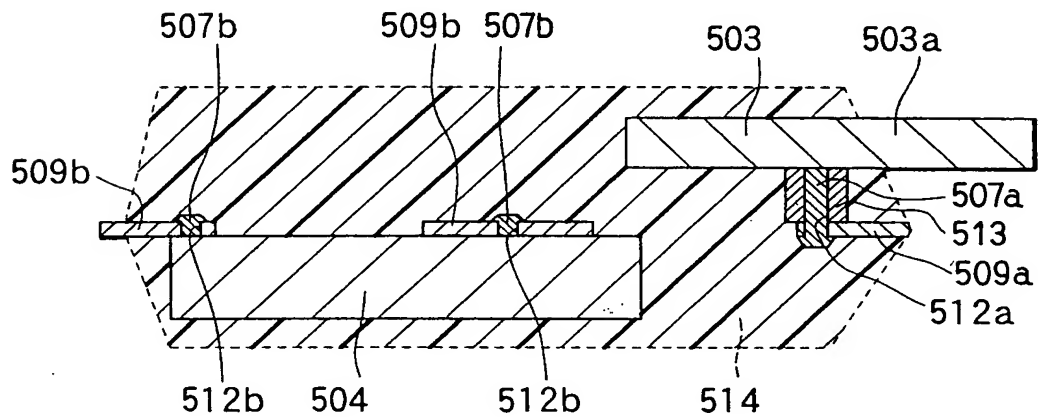


FIG. 29

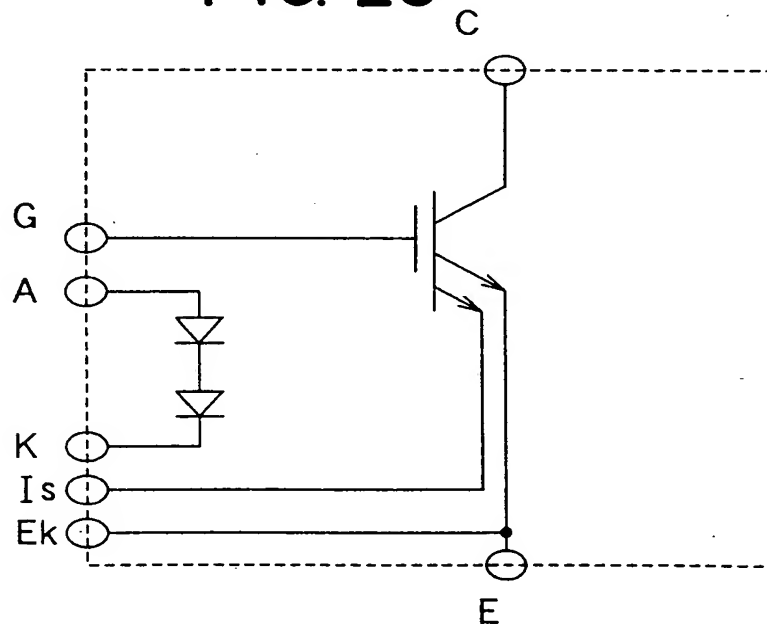


FIG. 30A

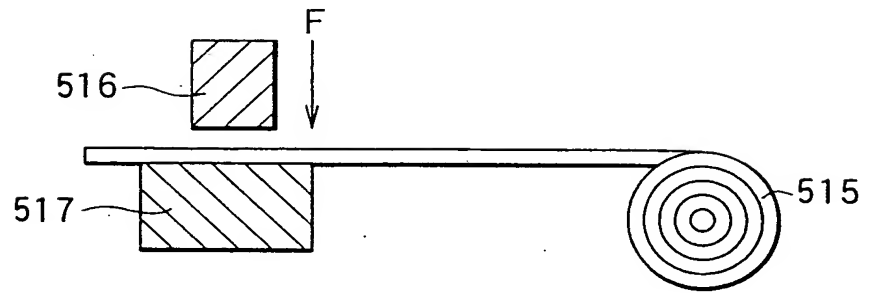


FIG. 30B

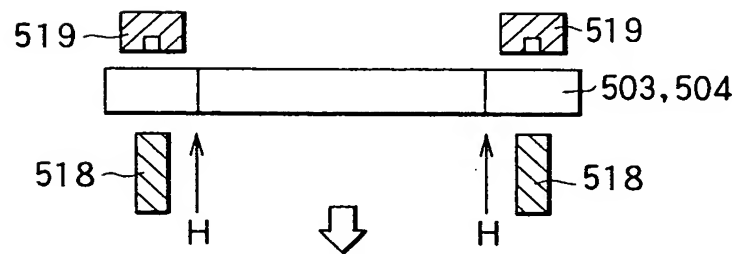


FIG. 30C

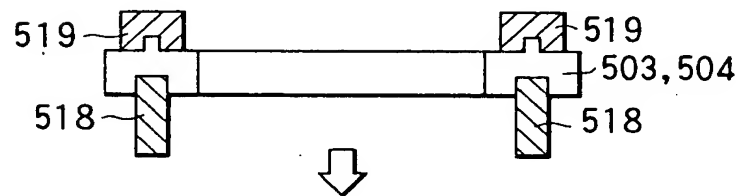


FIG. 30D



FIG. 31

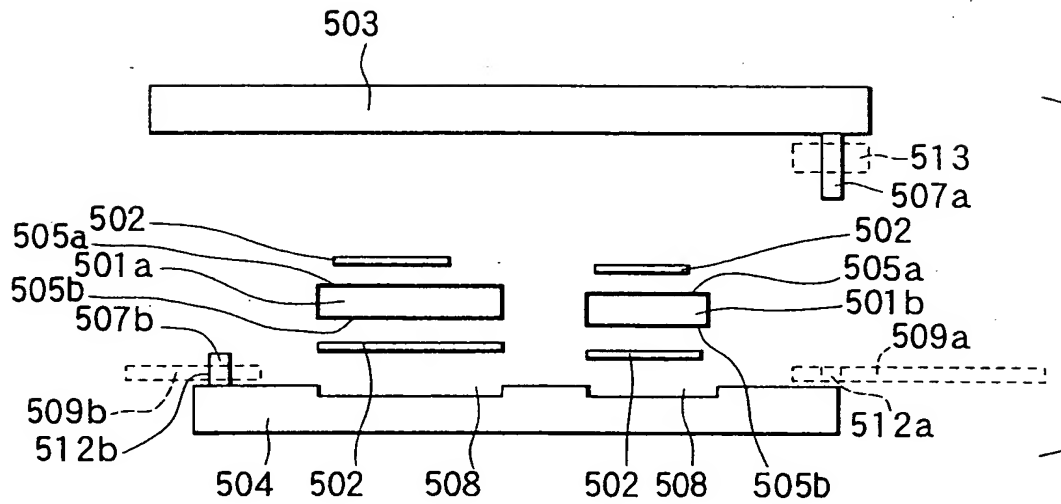


FIG. 32A

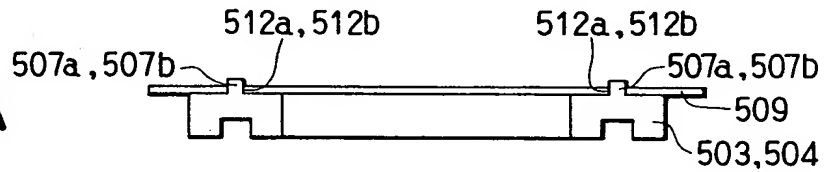


FIG. 32B

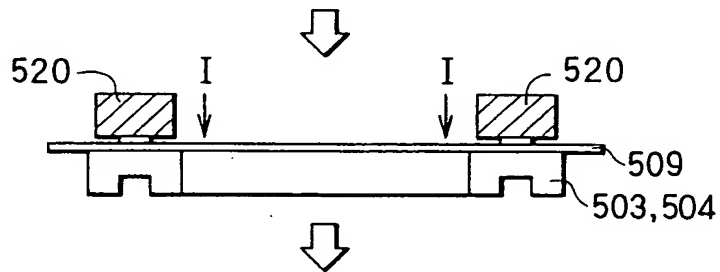


FIG. 32C

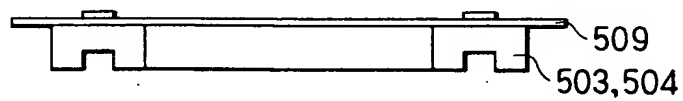


FIG. 33

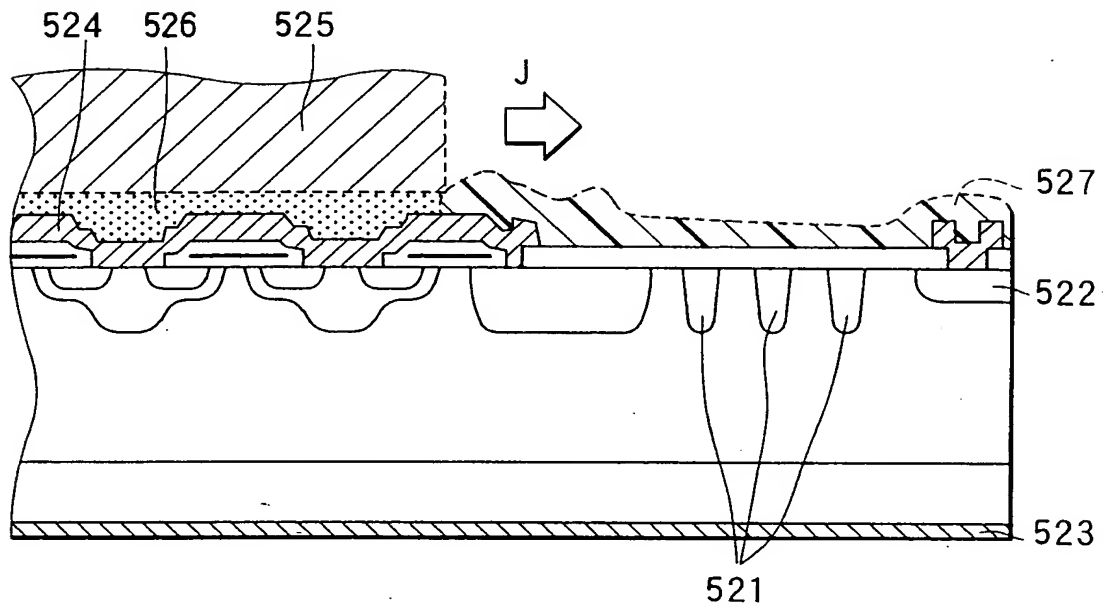


FIG. 34

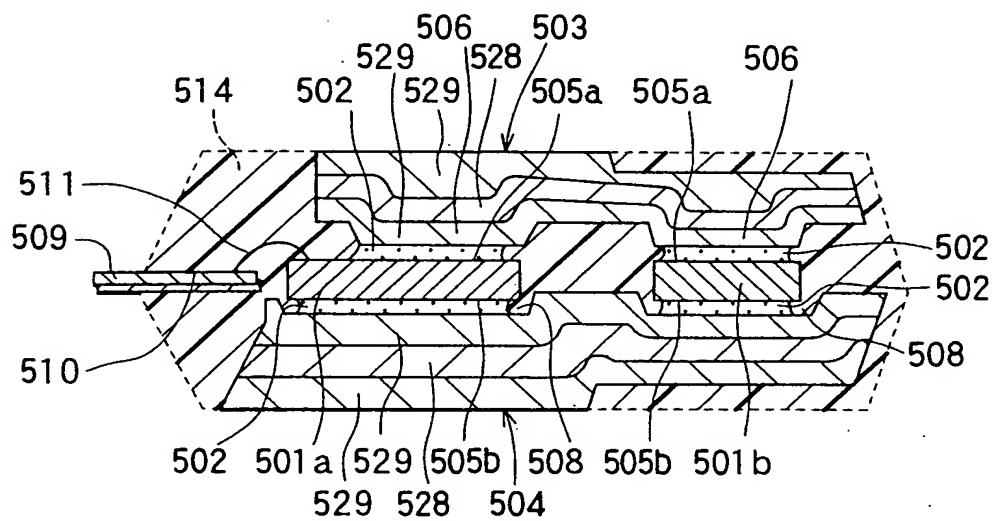


FIG. 35A

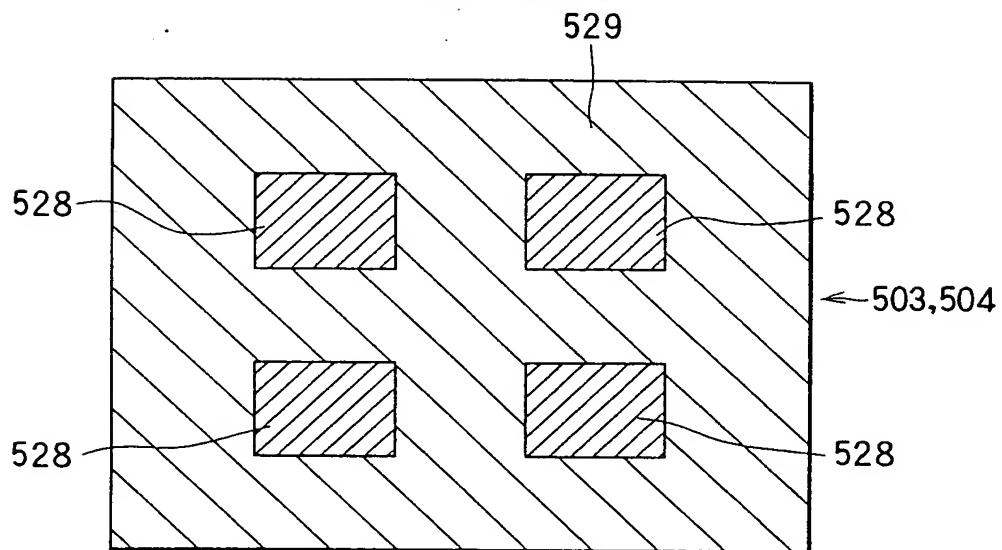


FIG. 35B

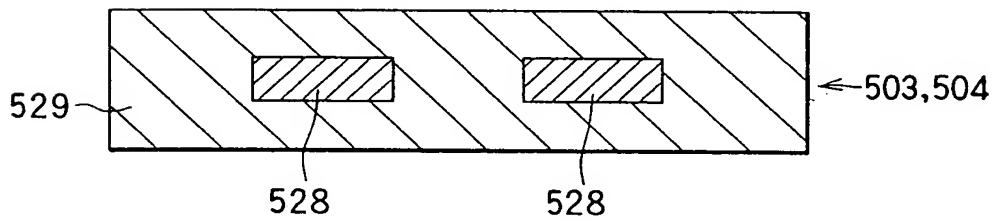


FIG. 36

